Silicon PNP Power Transistors 2SB1052

DESCRIPTION

·With TO-220Fa package
·Complement to type 2SD1480
·Low collector saturation voltage

APPLICATIONS

·For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

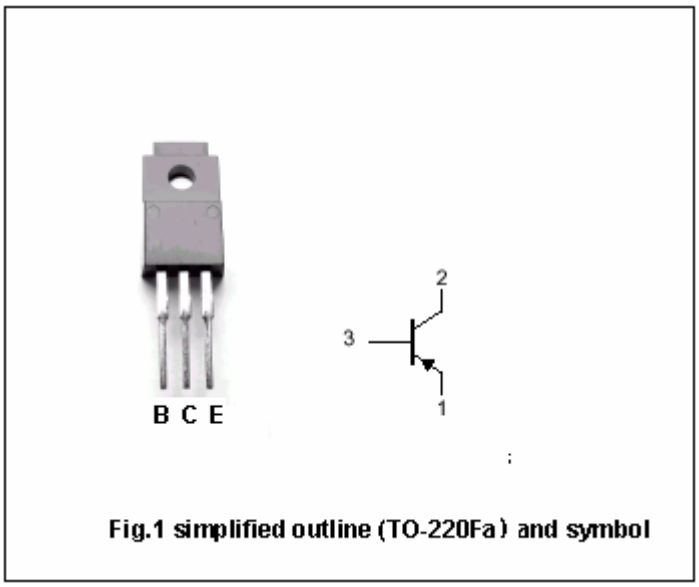

Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector -emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-2	A
I_{CM}	Collector current-peak		-4	A
P_C	Collector power dissipation	T_a=25□	2.0	W
		T_C=25□	25	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-30mA; I_B=0	-60			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2A ;I_B=-0.2A			-2.0	V
V_{BE}	Base-emitter on voltage	I_C=-1A ; V_{CE}=-4V			-1.2	V
I_{CES}	Collector cut-off current	V_{CE}=-60V; V_{BE}=0			-0.2	mA
I_{CEO}	Collector cut-off current	V_{CE}=-30V; I_B=0			-0.3	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-1.0	mA
h_{FE-1}	DC current gain	I_C=-0.1A ; V_{CE}=-4V	35			
h_{FE-2}	DC current gain	I_C=-1A ; V_{CE}=-4V	40		250	

Switching times

t_{on}	Turn-on time	I_C=-1A ;I_{B1}=-I_{B2}=-0.1A		0.1		μs
t_{stg}	Storage time			1.5		μs
t_f	Fall time			0.3		μs

◆ **h_{FE-2} Classifications**

R	Q	P
40-90	70-150	120-250

PACKAGE OUTLINE

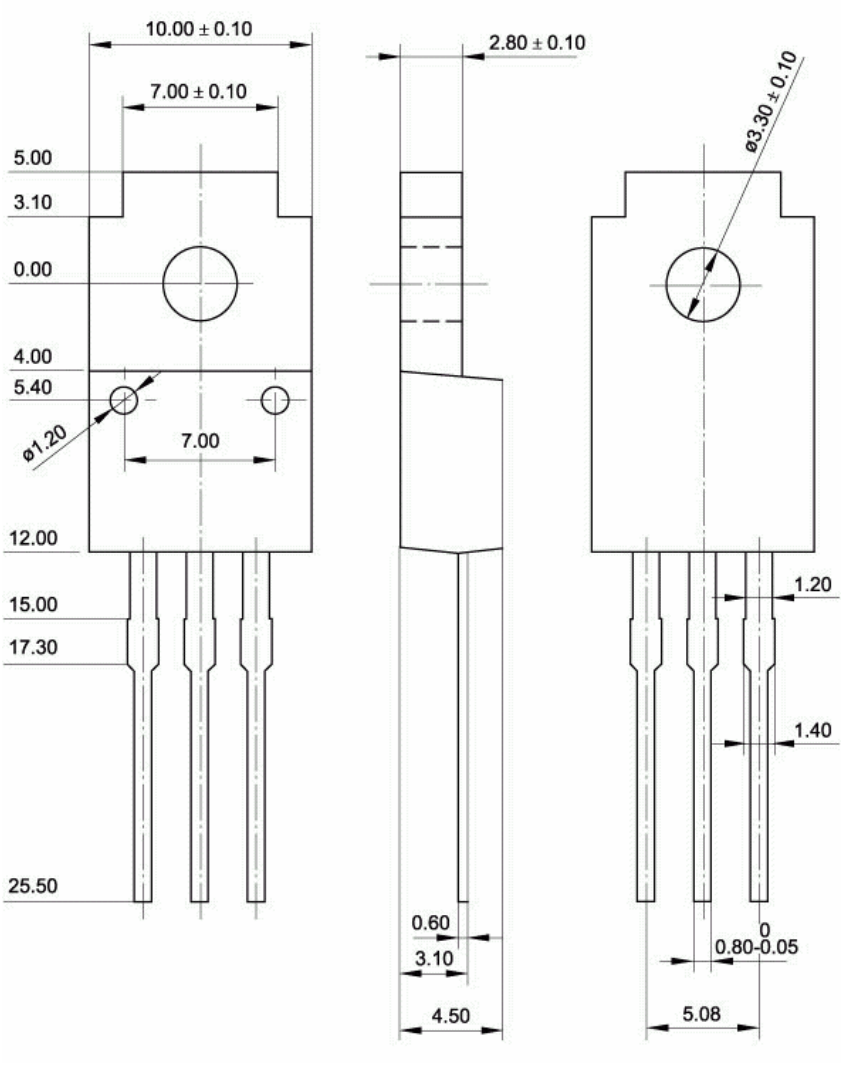

Fig.2 Outline dimensions (unindicated tolerance: ±0.15 mm)